



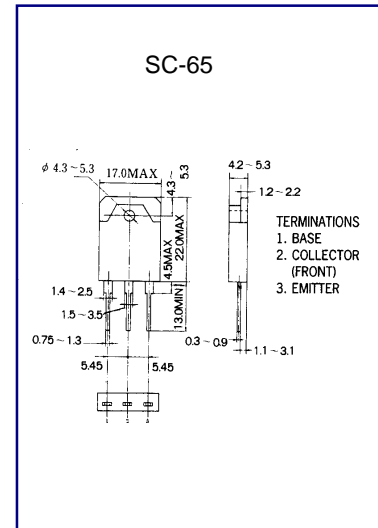
**2SB827**

**PNP PLANAR SILICON TRANSISTOR**

- PSW / D / DDC
- COMPLEMENTARY TO 2SD1063

**ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-60	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-50	V
Emitter-Base voltage	V <sub>EB0</sub>	-6	V
Collector Current (DC)	I <sub>C</sub>	-7	A
Collector Dissipation	P <sub>C</sub>	60	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV <sub>CB0</sub>	I <sub>C</sub> =-5 mA I <sub>E</sub> =0	-60			V
Collector Emitter Breakdown Voltage	BV <sub>CE0</sub>	I <sub>C</sub> =-10 mA R <sub>BE</sub> =∞	-50			V
Emitter Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> =-5mA I <sub>C</sub> =0	-6			V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =-60V I <sub>E</sub> =0			-0.1	mA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =-4V I <sub>C</sub> =0			-0.1	mA
*DC Current Gain	H <sub>fe</sub>	V <sub>CE</sub> =-2V I <sub>C</sub> =-1A	70		280	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-4A I <sub>B</sub> =-0.4A			-0.4	V